



EPITAXIAL-BASE NPN/PNP

POWER DARLINGTONS

The TIP120, TIP121 and TIP122 are silicon epitaxial-base NPN transistors in monolithic Darlington configuration in Jedec TO-220 plastic package, intended for use in power linear and switching applications.

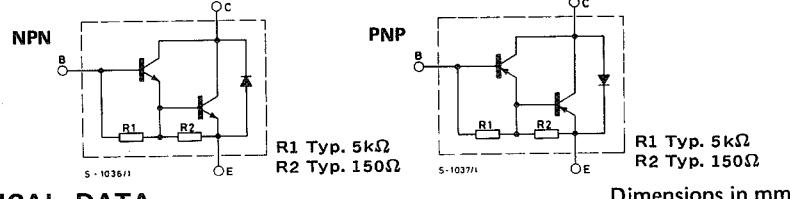
The complementary PNP types are the TIP125, TIP126 and TIP127 respectively.

ABSOLUTE MAXIMUM RATINGS

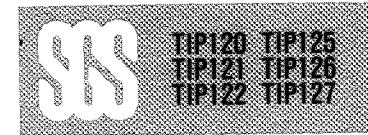
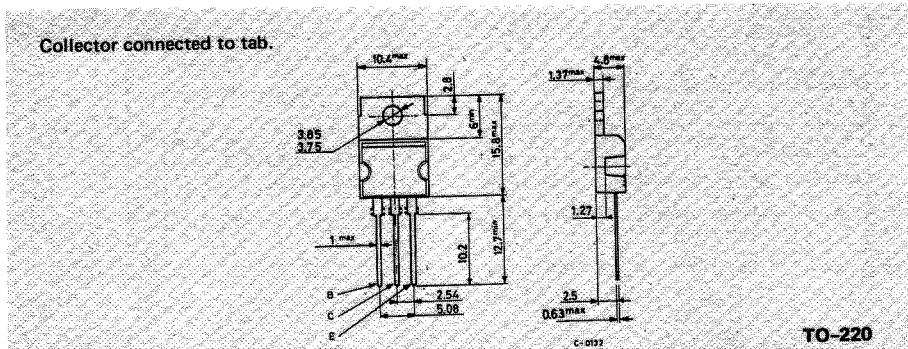
ABSOLUTE MAXIMUM RATINGS		NPN PNP*	TIP120 TIP125	TIP121 TIP126	TIP122 TIP127
V_{CBO}	Collector-base voltage ($I_E = 0$)		60V	80V	100V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)		60V	80V	100V
V_{EBO}	Emitter-base voltage ($I_C = 0$)			5V	
I_C	Collector current				5A
I_{CM}	Collector peak current				8A
I_B	Base current				0.1A
P_{tot}	Total power dissipationa at $T_{case} \leqslant 25^\circ\text{C}$ $T_{amb} \leqslant 25^\circ\text{C}$			65W	2W
T_{stg}	Storage temperature			$-65 \text{ to } 150^\circ\text{C}$	
T_J	Junction temperature			150°C	

* For PNP types voltage and current values are negative.

INTERNAL SCHEMATIC DIAGRAMS



MECHANICAL DATA



THERMAL DATA

$R_{th\ j-case}$	Thermal resistance junction-case	max	1.92	°C/W
$R_{th\ l-amb}$	Thermal resistance junction-ambient	max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector cutoff current ($I_B = 0$) for TIP120/5 $V_{CE} = 30V$ for TIP121/6 $V_{CE} = 40V$ for TIP122/7 $V_{CE} = 50V$		0.5 0.5 0.5		mA mA mA
I_{CBO}	Collector cutoff current ($I_E = 0$) for TIP120/5 $V_{CB} = 60V$ for TIP121/6 $V_{CB} = 80V$ for TIP122/7 $V_{CB} = 100V$		0.2 0.2 0.2		mA mA mA
I_{EBO}	Emitter cutoff current ($I_C = 0$) $V_{EB} = 5V$		2		mA
$V_{CEO\ (sus)}$ *	Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ for TIP120/5 for TIP121/6 for TIP122/7	60 80 100			V V V
$V_{CE\ (sat)}$ *	Collector-emitter saturation voltage $I_C = 3A \quad I_B = 12mA$ $I_C = 5A \quad I_B = 20mA$		2 4		V V
$V_{BE\ (on)}$ *	Base-emitter voltage $I_C = 3A \quad V_{CE} = 3V$		2.5		V
h_{FE} *	DC current gain $I_C = 0.5A \quad V_{CE} = 3V$ $I_C = 3A \quad V_{CE} = 3V$	1000 1000			—

* Pulsed: pulse duration = 300 μ s, duty cycle $\leq 2\%$